



May 2016

# FCPF150N65F

## N-Channel SuperFET<sup>®</sup> II FRFET<sup>®</sup> MOSFET

650 V, 24 A, 150 mΩ

### Features

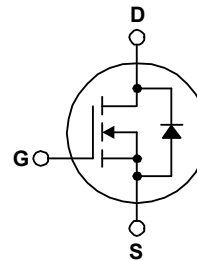
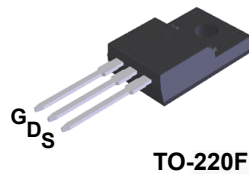
- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 133\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 72\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 361\text{ pF}$ )
- 100% Avalanche Tested
- RoHS Compliant

### Applications

- Telecom/Server Power Supplies
- Solar Inverters
- Computing Power Supplies
- FPD TV Power/Lighting

### Description

SuperFET<sup>®</sup> II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. SuperFET II FRFET<sup>®</sup> MOSFET combines a faster and more rugged intrinsic body diode performance with fast switching, aimed at achieving better reliability and efficiency especially in resonant switching applications. SuperFET II FRFET is very suitable for the switching power applications such as server/telecom power, Solar inverter, FPD TV power, computing power, lighting and industrial power applications.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCPF150N65F	Unit
$V_{DSS}$	Drain to Source Voltage	650	V
$V_{GSS}$	Gate to Source Voltage	- DC	$\pm 20$
		- AC ( $f > 1\text{ Hz}$ )	$\pm 30$
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	24*
		- Continuous ( $T_C = 100^\circ\text{C}$ )	14.9*
$I_{DM}$	Drain Current - Pulsed (Note 1)	72*	A
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	663	mJ
$I_{AR}$	Avalanche Current (Note 1)	4.7	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	2.98	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	50	
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	39
		- Derate Above $25^\circ\text{C}$	0.31
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

\*Drain current limited by maximum junction temperature.

### Thermal Characteristics

Symbol	Parameter	FCPF150N65F	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

FCPF150N65F — N-Channel SuperFET<sup>®</sup> II FRFET<sup>®</sup> MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF150N65F	FCPF150N65F	TO-220F	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 25^\circ\text{C}$	650	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 150^\circ\text{C}$	700	-	-	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$	-	0.72	-	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$	-	86	-	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.4\text{ mA}$	3	-	5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 12\text{ A}$	-	133	150	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 12\text{ A}$	-	22	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	2810	3737	pF
$C_{oss}$	Output Capacitance		-	91	121	pF
$C_{rss}$	Reverse Transfer Capacitance		-	0.77	-	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	54	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	361	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}$	-	72	94	nC
$Q_{gs}$	Gate to Source Gate Charge		-	15	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		(Note 4)	-	31	-
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	0.69	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\text{ }\Omega$	-	28	66	ns	
$t_r$	Turn-On Rise Time		-	15	40	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	-	73	156	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	6	22	ns

### Drain-Source Diode Characteristics

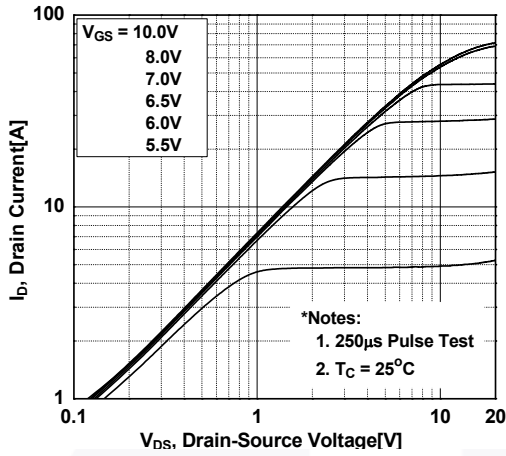
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	24	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	72	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 12\text{ A}$	-	-	1.2	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 12\text{ A}$	-	123	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{ A}/\mu\text{s}$	-	597	-	nC

#### Notes:

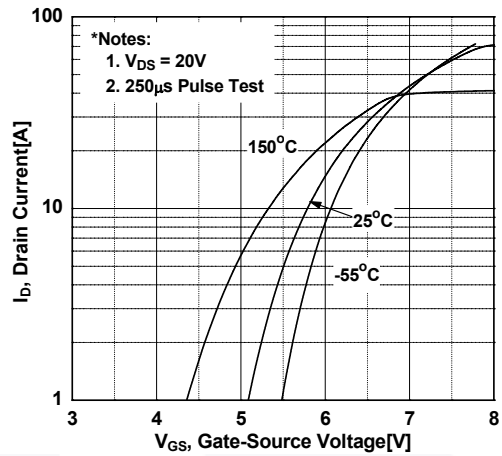
1. Repetitive rating: pulse width limited by maximum junction temperature.
2.  $I_{AS} = 4.7\text{ A}, R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 12\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq 380\text{ V}$ , Starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

## Typical Performance Characteristics

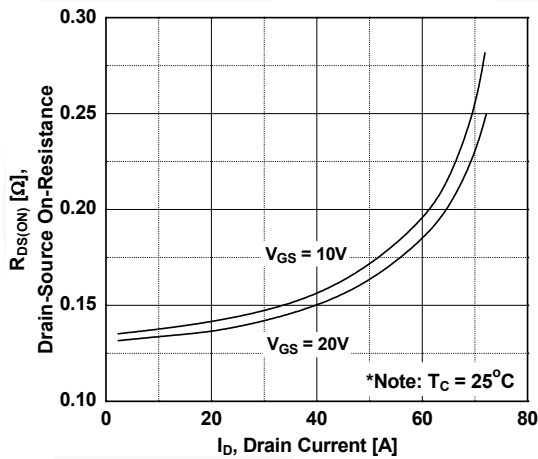
**Figure 1. On-Region Characteristics**



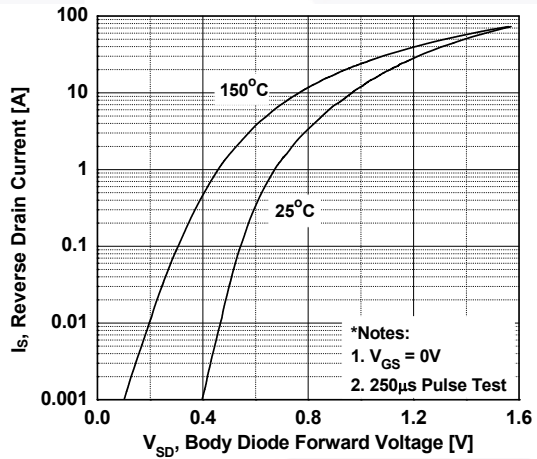
**Figure 2. Transfer Characteristics**



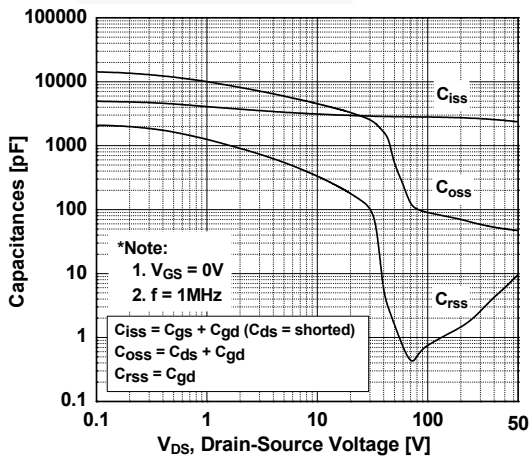
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



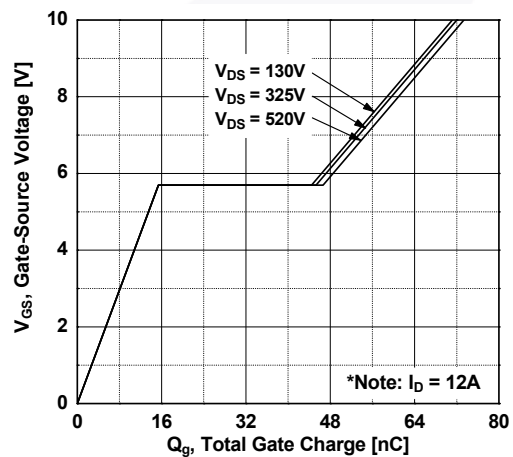
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

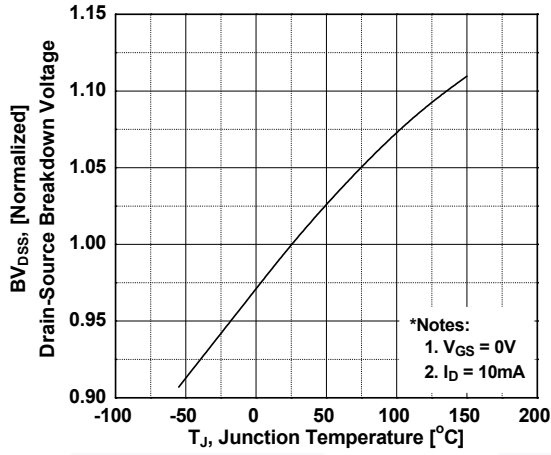


Figure 8. On-Resistance Variation vs. Temperature

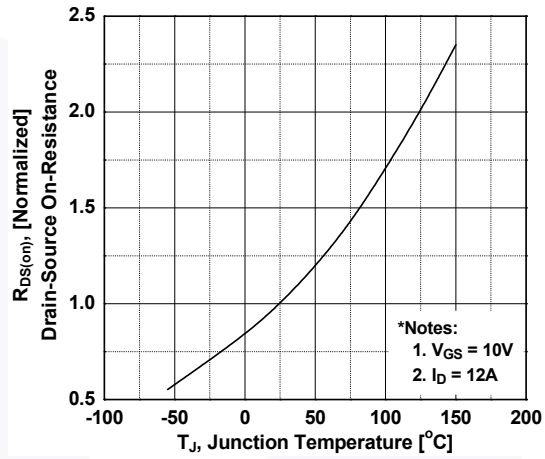


Figure 9. Maximum Safe Operating Area

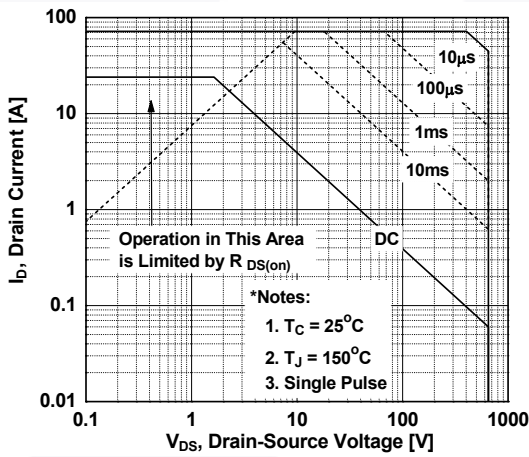


Figure 10. Maximum Drain Current vs. Case Temperature

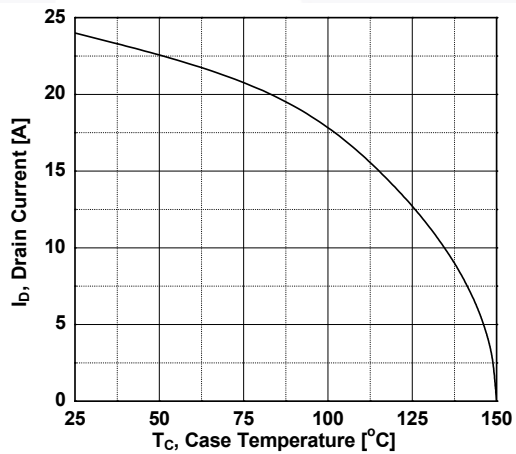
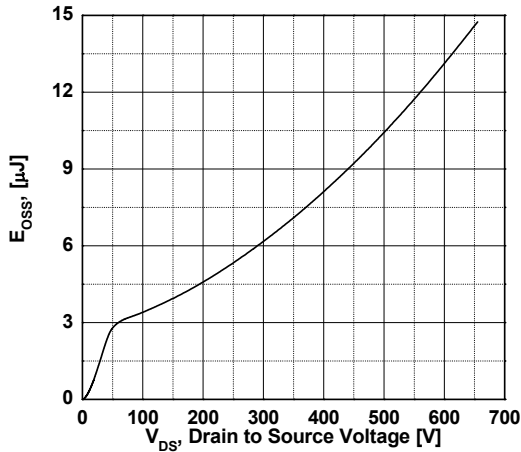
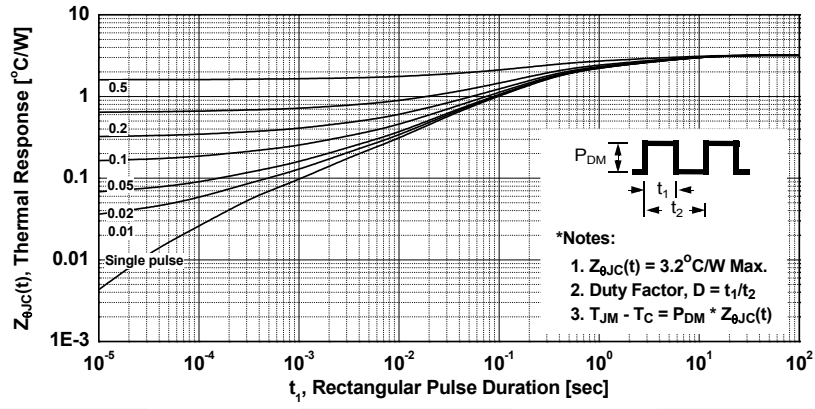


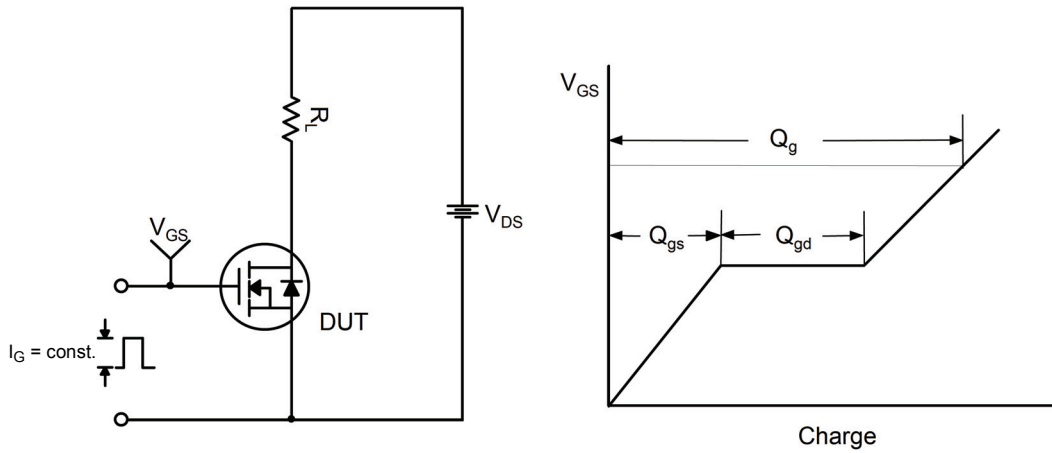
Figure 11. E\_oss vs. Drain to Source Voltage



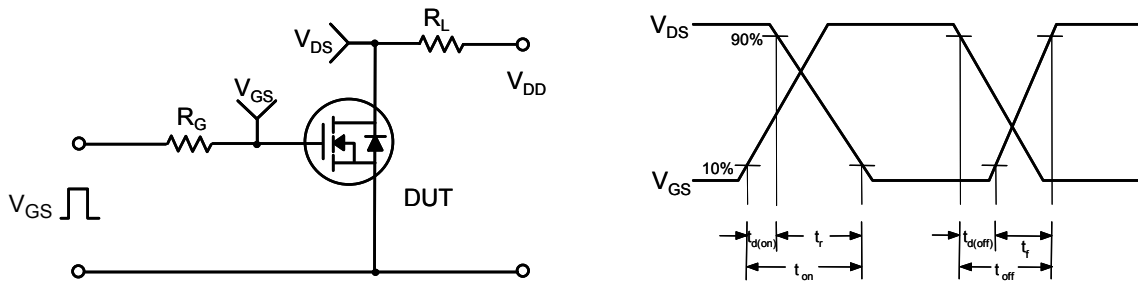
Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

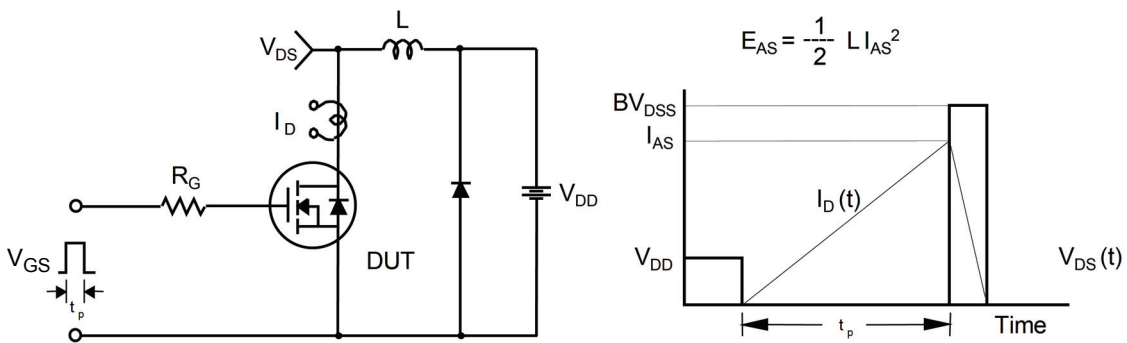




**Figure 13. Gate Charge Test Circuit & Waveform**



**Figure 14. Resistive Switching Test Circuit & Waveforms**



**Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms**

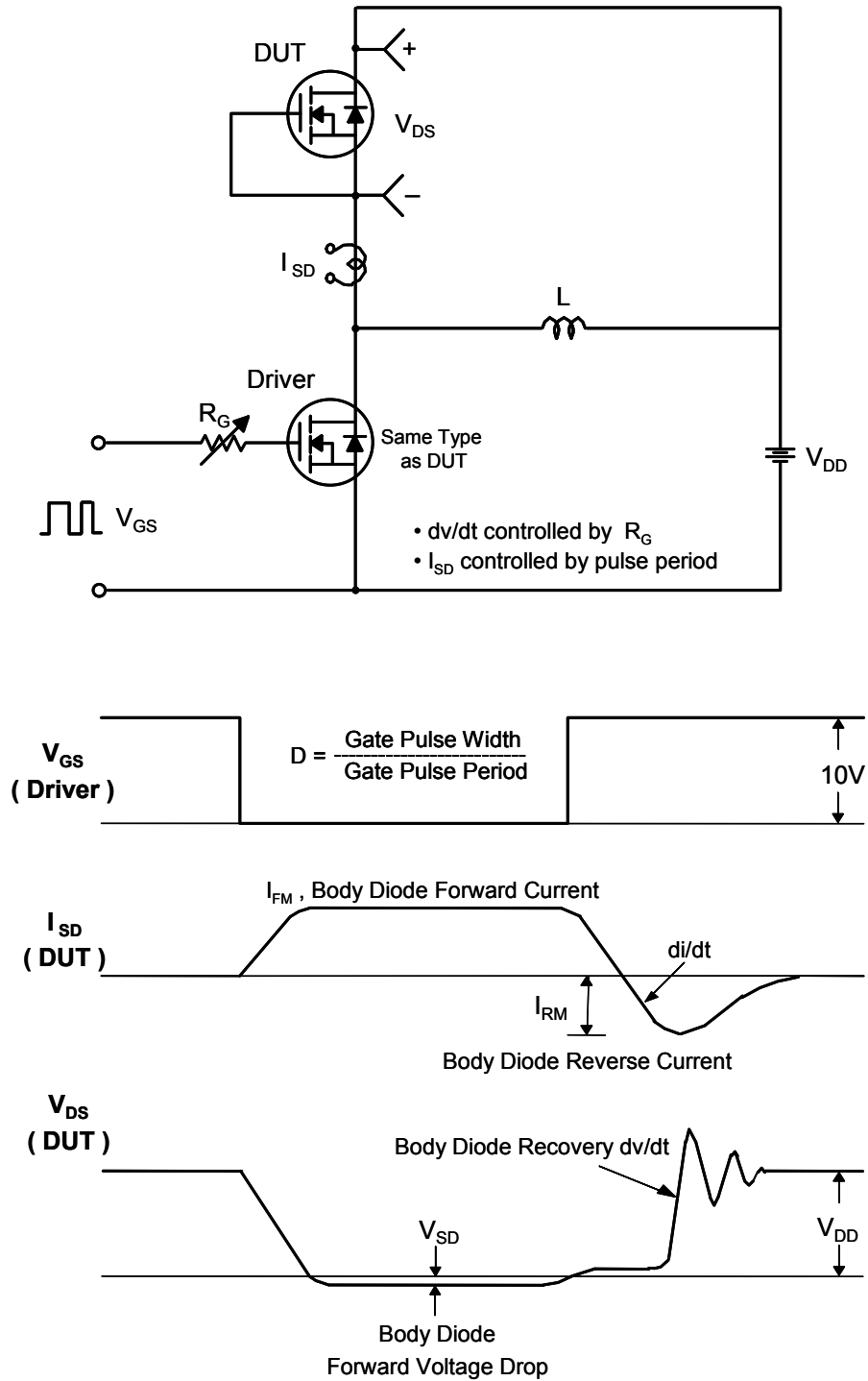


Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms







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